

IN THE CLAIMS

Please cancel claims 1-11 without prejudice.

1.-11. (Canceled)

12. (Currently Amended) An ~~apparatus~~ integrated circuit, comprising:

an indium-fluorine retrograde well inside a substrate, the indium-fluorine retrograde well including an indium concentration greater than about $3E18/cm^3$.

13. (Currently Amended) The ~~apparatus~~ integrated circuit of claim 12, wherein the indium-fluorine retrograde well includes an indium concentration three times, or more, greater than $3E18/cm^3$.

14. (Currently Amended) The ~~apparatus~~ integrated circuit of claim 12, wherein the indium-fluorine retrograde well includes a fluorine concentration between about $5E18/cm^3$ to about $3E20/cm^3$.

15. (Currently Amended) The ~~apparatus~~ integrated circuit of claim 12, wherein the indium-fluorine retrograde well includes an indium concentration peak at about 200\AA , or deeper, below the substrate surface.

16. (Original) An integrated circuit, comprising:

a substrate;

a gate structure formed on the substrate; and

an indium-fluorine retrograde well formed to a shallow depth below a surface of the substrate and beneath the gate structure.

17. (Original) The integrated circuit of claim 16, comprising an indium concentration above about 3×10^{18} .

18. (Currently Amended) The ~~apparatus~~ integrated circuit of claim 16, wherein the indium-fluorine retrograde well includes an indium concentration three times, or more, greater than $3 \times 10^{18}/\text{cm}^3$.

19. (Currently Amended) The ~~apparatus~~ integrated circuit of claim 16, wherein the indium-fluorine retrograde well includes a fluorine concentration between about $5 \times 10^{18}/\text{cm}^3$ to about $3 \times 10^{20}/\text{cm}^3$.

20. (Original) The integrated circuit of claim 16, wherein the indium has a concentration peak at about 200 \AA , or deeper, below the substrate surface.

21. (Currently Amended) An ~~apparatus~~ integrated circuit, comprising:

a gate structure overlying a silicon substrate;

source/drain regions inside the silicon substrate, the source/drain regions adjacent to opposing sides of the gate structure and extending slightly underneath the gate structure; and

a fluorine-indium retrograde well directly beneath the gate structure and between the source/drain regions, the fluorine-indium retrograde well including an indium concentration greater than $3 \times 10^{18}/\text{cm}^3$.

22. (Currently Amended) The ~~apparatus~~ integrated circuit of claim 21, wherein the fluorine-indium retrograde well is to provide a threshold voltage greater than about 360mV.

23. (Currently Amended) The ~~apparatus~~ integrated circuit of claim 21, wherein the fluorine-indium retrograde well includes an indium concentration peak at about 200Å, or deeper, below the substrate surface.

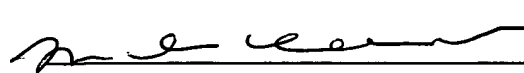
24. (Currently Amended) The ~~apparatus~~ integrated circuit of claim 21, wherein the gate structure has a gate length of about 60nm or less.

25. (Currently Amended) The ~~apparatus~~ integrated circuit of claim 21, wherein the fluorine-indium retrograde well includes an indium concentration three times, or more, greater than $3E18/cm^3$.

If there are any additional charges, please charge Deposit Account No. 02-2666.

Respectfully submitted,

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